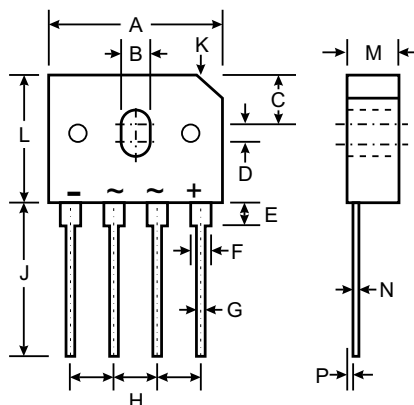


Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500VRMS
- Low Reverse Leakage Current
- Surge Overload Rating to 200A Peak
- Ideal for Printed Circuit Board Applications
- Plastic Material: UL Flammability Classification Rating 94V-0
- UL Listed Under Recognized Component Index, File Number E94661

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Marked on Body
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 5.0 Inch-pounds Maximum
- Marking: Date Code and Type Number
- Weight: 6.6 grams (approx.)



GBU		
Dim	Min	Max
A	21.8	22.3
B	3.5	4.1
C	7.4	7.9
D	1.65	2.16
E	2.25	2.75
G	1.02	1.27
H	4.83	5.33
J	17.5	18.0
K	3.2 X 45°	
L	18.3	18.8
M	3.30	3.56
N	0.46	0.56
P	0.76	1.0
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

Characteristic	Symbol	GBU 8005	GBU 801	GBU 802	GBU 804	GBU 806	GBU 808	GBU 810	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Working Peak Reverse Voltage	V _{RWM}								
DC Blocking Voltage	V _R								
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @ T _C = 100°C	I _O	8.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	200							A
Forward Voltage (per element) @ I _F = 4.0A	V _{FM}	1.0							V
Peak Reverse Current @ T _C = 25°C	I _R	5.0							μA
at Rated DC Blocking Voltage @ T _C = 125°C		500							
I ² t Rating for Fusing (t < 8.3ms) (Note 2)	I ² t	166							A ² s
Typical Junction Capacitance per Element (Note 3)	C _J	130							pF
Typical Thermal Resistance Junction to Case (Note 1)	R _{θJC}	2.2							°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150							°C

Notes: 1. United mounted on 50 x 50 x 1.6mm copper plate heatsink.
 2. Non-repetitive, for t > 1.0ms and < 8.3ms.
 3. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

